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Application Number		10/19/2003 -T80-			
Filing Date		11/21/03 Herewith			
First Named Inventor		Yuanming Chen, et al.			
Group Art Unit		2813			
Examiner Name		Jack S J Chen			
Attorney Docket No.		TI-35022.1			

U.S. PATENT DOCUMENTS						
Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	CA	RYUTA TSUCHIYA ET AL., "Femto-Second CMOS Technology with High-k Offset Spacer and SiN Gate Dielectric with Oxygen-Enriched Interface" IEEE 2002 Symposium on VLSI Technology Digest of Technical Papers	
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